TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

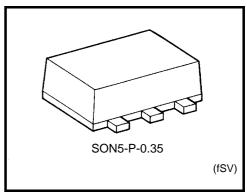
TC7SH125FS

Bus Buffer

Features

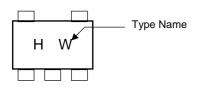
High speed: t_{pd} = 3.8 ns (typ.) at V_{CC} = 5 V Low power dissipation: I_{CC} = 2 μ A (max) at Ta = 25°C High noise immunity: V_{NIH} = V_{NIL} = 28% V_{CC} (min) 5.5V tolerant input.

Wide operating voltage range: V_{CC} (opr) = 2~5.5 V

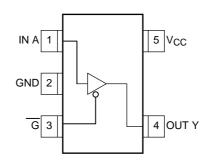


Weight: 0.001 g (Typ.)

Marking



Pin Assignment (top view)



Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Supply voltage range	Vcc	-0.5~7.0	V
DC input voltage	V _{IN}	-0.5~7.0	V
DC output voltage	V _{OUT}	-0.5~V _{CC} + 0.5	V
Input diode current	lıĸ	-20	mA
Output diode current	lok	±20	mA
DC output current	lout	±25	mA
DC V _{CC} /ground current	Icc	±50	mA
Power dissipation	PD	50	mW
Storage temperature	T _{stg}	-65~150	°C

Logic Diagram



Truth Table

G	А	Υ
Н	Х	Z
L	L	L
L	Н	Н

Recommended Operating Conditions

Characteristics	Symbol	Rating	Unit	
Supply voltage	V _{CC}	2.0~5.5	V	
Input voltage	V _{IN}	0~5.5	V	
Output voltage	V _{OUT}	0~V _{CC}	V	
Operating temperature	T _{opr}	-40~85	°C	
Input rise and fall time	dt/dv	0~100 (V _{CC} = 3.3 ± 0.3 V)	ns/V	
input rise and rail time	ui/uv	$0 \sim 20 \; (V_{CC} = 5 \pm 0.5 \; V)$	115/ V	

Electrical Characteristics

DC Characteristics

Characteristics Symbol		Test	Test Condition			Ta = 25°C			Ta = -40~85°C		
		Circuit				Min	Тур.	Max	Min	Max	Unit
High-level input					1.5	_	_	1.5	_		
voltage	V _{IH}	_		_		V _{CC} × 0.7	_	_	V _{CC} × 0.7	_	V
Low-level input			_		2.0	_		0.50	_	0.50	V
voltage	V _{IL}	_			3.0~ 5.5	_		V _{CC} × 0.3	_	V _{CC} × 0.3	
				Ι _{ΟΗ} = -50 μΑ	2.0	1.9	2.0	_	1.9	_	V
			V _{IN} = V _{IH} or VIL		3.0	2.9	3.0	_	2.9	_	
High-level output voltage	VoH				4.5	4.4	4.5	_	4.4	_	
				$I_{OH} = -4 \text{ mA}$	3.0	2.58		_	2.48	_	
				$I_{OH} = -8 \text{ mA}$	4.5	3.94			3.80	_	
				Ι _{ΟL} = 50 μΑ	2.0	_	0	0.1		0.1	V
					3.0	_	0	0.1	_	0.1	
Low-level output voltage	V_{OL}	_	$V_{IN} = V_{IH}$		4.5	_	0	0.1	_	0.1	
Ü				I _{OL} = 4 mA	3.0	_	_	0.36	_	0.44	
				I _{OL} = 8 mA	4.5	_	_	0.36	_	0.44	
3-state output off-state current	l _{OZ}	_	V _{IN} = V _{IH} or V _{IL} V _{OUT} = V _{CC} or GND		5.5	_	_	±0.25	_	±2.5	μА
Input leakage current	I _{IN}	_	V _{IN} = 5.5 V or GND		0~ 5.5	_	_	±0.1	_	±1.0	μА
Quiescent supply current	Icc	_	V _{IN} = V _{CC} o	5.5			2.0	_	20.0	μА	

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AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Circuit	Test Condition		n Ta = 25°C			Ta = -4	0~85°C	Unit	
Characteristics	Зуппон			V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Min	Max	Unit
				3.3 ± 0.3	15	_	5.6	8.0	1.0	9.5	
Propagation delay	t _{pLH}	_	_	3.3 ± 0.3	50	_	8.1	11.5	1.0	13.0	ns
time	t_{pHL}			50.05	15	_	3.8	5.5	1.0	6.5	
				5.0 ± 0.5	50	_	5.3	7.5	1.0	8.5	
	t _{pZL}	_	_	3.3 ± 0.3	15		5.4	8.0	1.0	9.5	ns
3-state output					50		7.9	11.5	1.0	13.0	
enable time	^t pZH			5.0 ± 0.5	15		3.6	5.1	1.0	6.0	
				5.0 ± 0.5	50		5.1	7.1	1.0	8.0	
3-state output	t_{pLZ}			3.3 ± 0.3	50		9.5	13.2	1.0	15.0	ns
disable time	t _{pHZ}			5.0 ± 0.5	50		6.1	8.8	1.0	10.0	115
Input capacitance	C _{IN}	_		_			4	10	_	10	pF
Output capacitance	C _{OUT}	_		_			6	_	_	_	pF
Power dissipation capacitance	C _{PD}	_			(Note)	_	14	_	_	_	pF

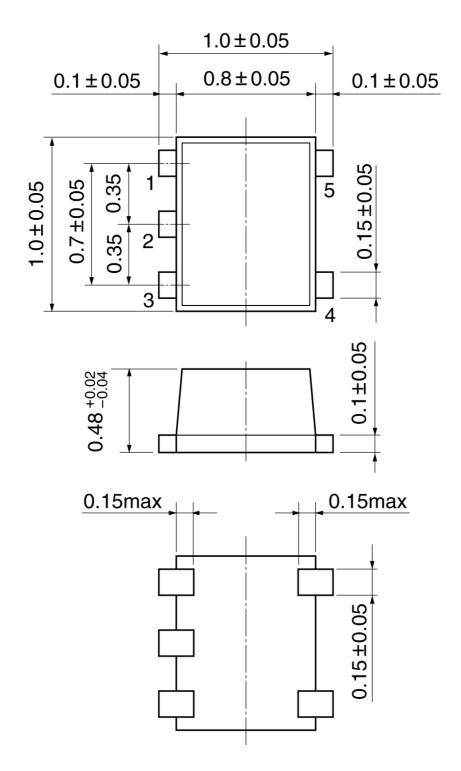
Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

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Average operating current can be obtained by the equation:

$$I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

Package Dimensions



Weight: 0.001 g (typ.)

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